New Product

Vishay Siliconix

P-Channel 60-V (D-S) MOSFET

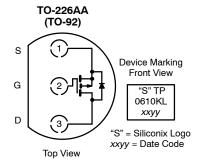
PRODUCT SUMMARY							
V _{(BR)DSS(min)} (V)	$r_{DS(on)}(\Omega)$	V _{GS(th)} (V)	I _D (A)				
-60	6 @ V _{GS} = -10 V	−1 to −3.0	-0.27				
	10 @ V _{GS} = -4.5 V	-110-3.0	-0.21				

FEATURES

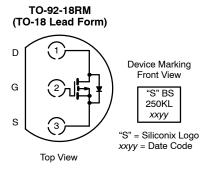
TrenchFET® Power MOSFET
ESD Protected: 2000 V

APPLICATIONS

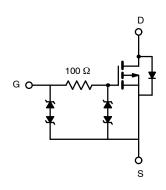
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply, Converter Circuits
- Motor Control







Ordering Information: BS250KL-TR1



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)								
Parameter		Symbol	Limit	Unit				
Drain-Source Voltage		V_{DS}	-60	.,				
Gate-Source Voltage		V _{GS}	±20	V				
Continuous Drain Current	T _A = 25°C	I _D	-0.27					
	T _A = 70°C		-0.22	Α				
Pulse Drain Current ^a		I _{DM}	-1.0					
Power Dissipation	T _A = 25°C	PD	0.8	w				
	T _A = 70°C	۵' ا	0.51	VV				
Maximum Junction-to-Ambient		R _{thJA}	156	°C/W				
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C				

Notes

a. Pulse width limited by maximum junction temperature.

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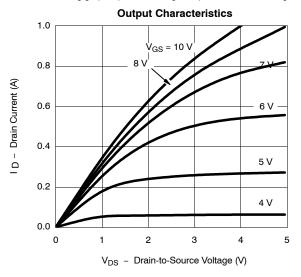
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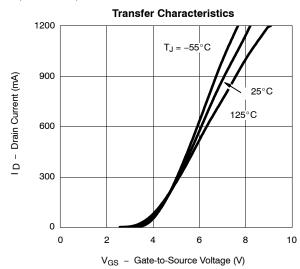


SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = -10 \mu A$	-60			V
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	-1	-2.1	-3.0	1 °
Gate-Body Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	μΑ
		V_{DS} = 0 V, V_{GS} = ± 10 V			±200	nA
	IGSS	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}, T_J = 85^{\circ}\text{C}$			±500	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			±100	
Zero Gate Voltage Drain Current		$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μА
	DSS	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	
On-State Drain Current ^a		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}$	-50			mA
	I _{D(on)}	$V_{DS} = -10 \text{ V}, V_{GS} = -10 \text{ V}$	-600			
Drain-Source On-Resistance ^a	r _{DS(on)}	V_{GS} = -4.5 V, I_D = -25 mA		5.5	10	Ω
		$V_{GS} = -10 \text{ V}, I_D = -500 \text{ mA}$		3.1	6	
		$V_{GS} = -10 \text{ V}, I_D = -500 \text{ mA}, T_J = 125^{\circ}\text{C}$		4.7	9	
Forward Transconductancea	9fs	$V_{DS} = -10 \text{ V}, I_D = -100 \text{ mA}$		180		mS
Diode Forward Voltage ^a	V _{SD}	$I_S = -200 \text{ mA}, V_{GS} = 0 \text{ V}$		-0.9	-1.4	V
Dynamic ^b						
Total Gate Charge	Qg	V_{DS} = -30 V, V_{GS} = -15 V, I_D \cong -500 mA		1.7	3	
Gate-Source Charge	Q _{gs}			0.26		nC
Gate-Drain Charge	Q _{gd}			0.46		
Gate Resistance	R _g			285		Ω
Turn-On Time	t _{d(on)}	V_{DD} = -25 V, R_L = 150 Ω $I_D \cong -150$ mA, V_{GEN} = -10 V R_q = 10 Ω		2.4	5	ns
	t _r			15.5	25	
Turn-Off Time	t _{d(off)}			21	35	
	t _f	•		12.5	20	

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

For the following graphs, p-channel negative polarities for all voltage and current values are represented as positive values.





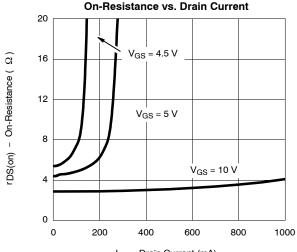
Notes
a. Pulse test: PW ≤300 ms duty cycle ≤2%.
b. Guaranteed by design, not subject to production testing.

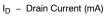


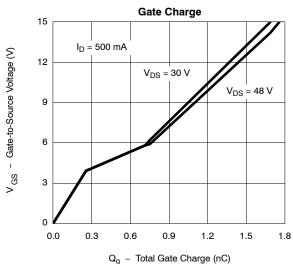
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TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

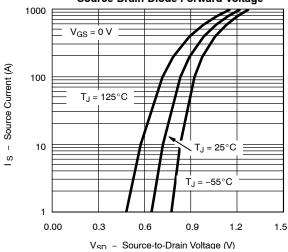
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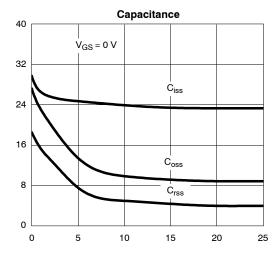




Source-Drain Diode Forward Voltage

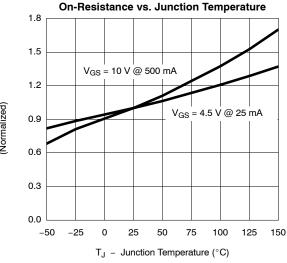


Capacitance (pF)

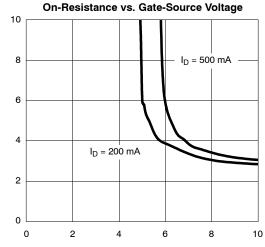


V_{DS} - Drain-to-Source Voltage (V)





8 rDS(on) – On-Resistance (Ω)



V_{GS} - Gate-to-Source Voltage (V)

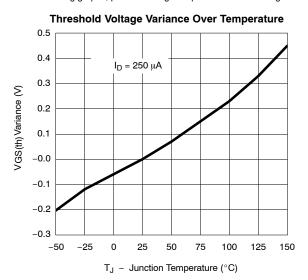
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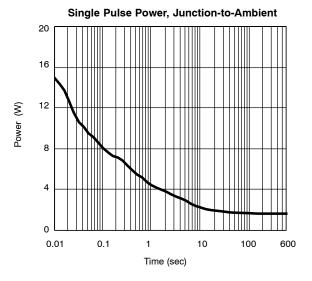
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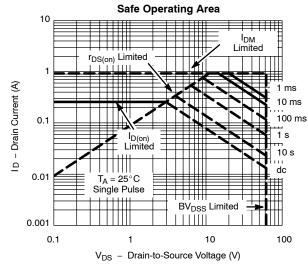


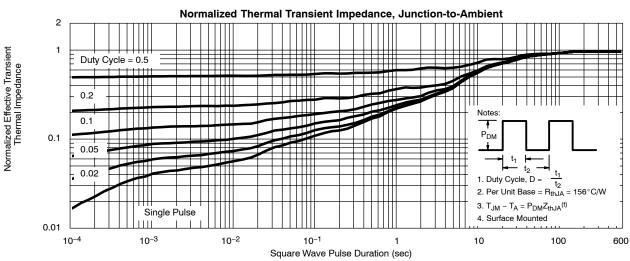
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

For the following graphs, p-channel negative polarities for all voltage and current values are represented as positive values.











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